

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) An exposure apparatus setting a prescribed light exposure in exposure for forming a resist pattern with an optical system, comprising:

at least two spaced apart illuminance meters provided on the emission side of ~~single~~ said optical system;

average illuminance operation means operating average illuminance on the basis of measured illuminance values obtained from said illuminance meters; and

light exposure control means controlling the light exposure on the basis of information obtained from said average illuminance operation means.

2. (Original) The exposure apparatus according to claim 1, wherein

said average illuminance operation means includes means obtaining said average illuminance with remaining said measured illuminance values except those of measured illuminance values exceeding a prescribed threshold in illuminance measurement.

3. (Withdrawn) An exposure method setting a prescribed light exposure in exposure for forming a resist pattern with an optical system, comprising:

an average illuminance operating step of operating average illuminance on the basis of measured illuminance values obtained from at least two illuminance meters provided on the emission side of single said optical system; and

a light exposure control step of controlling the light exposure on the basis of information obtained from said average illuminance operating step.

4. (Withdrawn) The exposure method according to claim 3, wherein said average illuminance operating step includes a step of obtaining said average illuminance with remaining said measured illuminance values except those of measured illuminance values exceeding a prescribed threshold in illuminance measurement.

5. (Withdrawn) A semiconductor device fabricated with an exposure method comprising an average illuminance operating step of operating average illuminance on the basis of measured illuminance values obtained from at least two illuminance meters provided on the emission side of a single optical system and a light exposure control step of controlling the light exposure on the basis of information obtained from said average illuminance operating step.

6. (Original) An exposure apparatus setting a prescribed light exposure in exposure for forming a resist pattern, comprising:

illuminance measuring means performing illuminance measurement before exposing an $(N - 1)$ th (N : integer) wafer, illuminance measurement after exposing said $(N - 1)$ th wafer and illuminance measurement during at least single exposure of said $(N - 1)$ th wafer; and

light exposure decision means deciding illuminance for an N -th wafer from measurement results obtained from said illuminance measuring means for deciding the light exposure for exposing said N -th wafer.

7. (Original) The exposure apparatus according to claim 6, wherein said light exposure decision means includes:

relational expression operation means obtaining a relational expression of illuminance and an exposure time from illuminance measurement results obtained from said illuminance measuring means, and

first illuminance operation means obtaining illuminance at the time of starting exposure of said N-th wafer and illuminance at the time of ending said exposure from said relational expression obtained by said relational expression operation means.

8. (Original) The exposure apparatus according to claim 7, wherein

said N-th wafer is provided with a plurality of shot areas, and

said light exposure decision means further includes:

second illuminance operation means obtaining illuminance every shot of said N-th wafer,

and

exposure time operation means obtaining an exposure time every shot of said N-th wafer.

9. (Withdrawn) An exposure method setting a prescribed light exposure in exposure for forming a resist pattern, comprising:

an illuminance measuring step of performing illuminance measurement before exposing an (N – 1)th (N: integer) wafer, illuminance measurement after exposing said (N – 1)th wafer and illuminance measurement during at least single exposure of said (N – 1)th wafer; and

a light exposure decision step of deciding illuminance for an N-th wafer from measurement results obtained from said illuminance measuring step for deciding the light exposure for exposing said N-th wafer.

10. (Withdrawn) The exposure method according to claim 9, wherein

said light exposure decision step includes:

a relational expression operation step of obtaining a relational expression of illuminance and an exposure time from illuminance measurement results obtained from said illuminance measuring step, and

a first illuminance operation step of obtaining illuminance at the time of starting exposure of said N-th wafer and illuminance at the time of ending said exposure from said relational expression obtained in said relational expression operation step.

11. (Withdrawn) The exposure method according to claim 10, wherein

said N-th wafer is provided with a plurality of shot areas, and

said light exposure decision step further includes:

a second illuminance operation step of obtaining illuminance every shot of said N-th wafer, and

an exposure time operation step of obtaining an exposure time every shot of said N-th wafer.

12. (Withdrawn) A semiconductor device fabricated with an exposure method, setting a prescribed light exposure in exposure for forming a resist pattern, comprising an illuminance measuring step of performing illuminance measurement before exposing an (N - 1)th (N: integer) wafer, illuminance measurement after exposing said (N - 1)th wafer and illuminance measurement during at least single exposure of said (N - 1)th wafer and a light exposure decision step of deciding illuminance for an N-th wafer from measurement results obtained from said illuminance measuring step for deciding the light exposure for exposing said N-th wafer.